

DECLARATION OF SOLE INVENTOR FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: "Methods of Forming a Phosphorus Doped Silicon Dioxide Comprising Layer, and Methods of Forming Trench Isolation in the Fabrication of Integrated Circuitry", the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations § 1.56.


PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such

willful false statement may jeopardize the validity of the application or any patent issued therefrom.

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Full name of sole inventor: **Brian A. Vaartstra**
Inventor's Signature: 
Date: 26 June 2003
Residence: **Nampa, Idaho**
Citizenship: **Canada**
Post Office Address: **3417 Braden Lane, Nampa, ID 83686**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. Unknown
Filing Date Filed Herewith
Inventor Brian A. Vaartstra
Assignee Micron Technology, Inc.
Group Art Unit Unknown
Examiner Unknown
Attorney's Docket No. MI22-2308
Title: Methods of Forming a Phosphorus Doped Silicon Dioxide Comprising Layer,
and a Method of Forming Trench Isolation in the Fabrication of Integrated
Circuitry

POWER OF ATTORNEY BY ASSIGNEE AND CERTIFICATE BY ASSIGNEE
UNDER 37 CFR § 3.73(b)

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

MICRON TECHNOLOGY, INC., the Assignee of the entire right, title and
interest in the above-identified patent application by assignment attached hereto,
hereby appoints the attorneys and agents of the firm of WELLS ST. JOHN P.S.,
listed as follows:

David P. Roberts	Reg. No. 23,032
Randy A. Gregory	Reg. No. 30,386
Mark S. Matkin	Reg. No. 32,268
Deepak Malhotra	Reg. No. 33,560
Mark W. Hendricksen	Reg. No. 32,356
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George G. Grigel	Reg. No. 31,166
Keith D. Grzelak	Reg. No. 37,144
James D. Shaurette	Reg. No. 39,833
James E. Lake	Reg. No. 44,854
D. Brent Kenady	Reg. No. 40,045
Jennifer J. Taylor	Reg. No. 48,711
Robert C. Hyta	Reg. No. 46,791
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and also attorneys Michael L. Lynch (Reg. No. 30,871), Charles B. Brantley II (Reg. No. 38,086) and Russel D. Slifer (Reg. No. 39,838) of Micron Technology, Inc., as its attorneys with full power of substitution to prosecute this application and transact all business in the Patent and Trademark Office connected therewith.

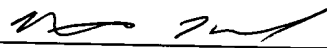
The Assignee certifies that the above-identified Assignment has been reviewed and to the best of Assignee's knowledge and belief, title is in the Assignee, and a copy of the Assignment is submitted herewith.

Please direct all correspondence regarding this application to:

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MICRON TECHNOLOGY, INC.

Dated: 7-1-03

By: 

Name: Michael L. Lynch, Esq.

Title: Chief Patent Counsel

Attachments: Copy of Assignment; Copy of Board of Directors' Resolution